



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

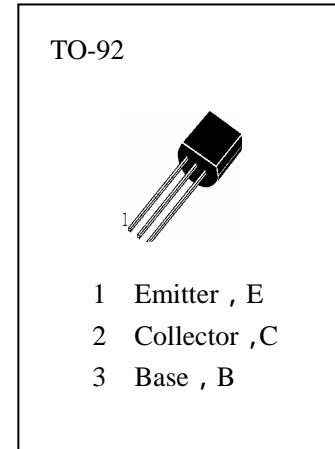
**H1300**

### STROBE FLASH APPLICATIONS

### MEDIUM POWER AMPLIFIER APPLICATIONS

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$	Storage Temperature.....	-55~150
$T_j$	Junction Temperature.....	150
$P_C$	Collector Dissipation.....	750mW
$V_{CBO}$	Collector-Base Voltage.....	-20V
$V_{CEO}$	Collector-Emitter Voltage.....	-10V
$V_{EBO}$	Emitter-Base Voltage.....	-6V
$I_C$	Collector Current.....	-2A
$I_{CP}$	Collector Current ( Pulse ) .....	-5A



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BVCBO$	Collector-Base Breakdown Voltage	-20			V	$I_C=-100 \mu A, I_E=0$
$BVCEO$	Collector-Emitter Breakdown Voltage	-10			V	$I_C=-10mA, I_B=0$
$BVEBO$	Emitter-Base Breakdown Voltage	-6			V	$I_E=-1mA, I_C=0$
$HFE(1)$	DC Current Gain	140		600		$V_{CE}=-1V, I_C=-500mA$
$HFE(2)$		70				$V_{CE}=-1V, I_C=-2A$
$VCE(sat)$	Collector- Emitter Saturation Voltage			-0.5	V	$I_C=-2A, I_B=-50mA$
$VBE$	Base-Emitter Voltage			-1.5	V	$V_{CE}=-1V, I_C=-2A$
$ICBO$	Collector Cut-off Current			-100	nA	$V_{CB}=-20V, I_E=0$
$ICEO$	Collector Cut-off Current			-100	nA	$V_{CE}=-10V, I_B=0$
$IEBO$	Emitter Cut-off Current			-100	nA	$V_{EB}=-6V, I_C=0$
$f_T$	Current Gain-Bandwidth Product	140			MHz	$V_{CE}=-1V, I_C=-0.5A$
$C_{ob}$	Output Capacitance		50		pF	$V_{CB}=-10V, I_E=0, f=1MHz$

### hfe Classification

Y

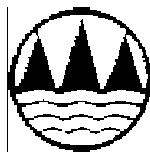
GR

BL

140—280

200—400

300—600



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